

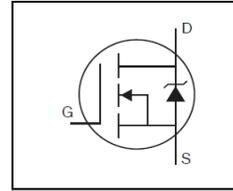
Features

- Advanced Process Technology
- Ultra Low On-Resistance
- Logic Level Gate Drive
- 150°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

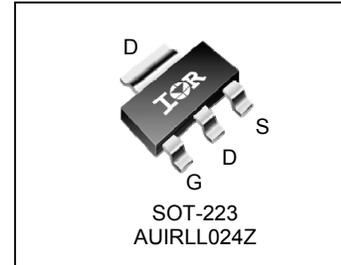
Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

HEXFET® Power MOSFET



| | |
|--------------------------|-------------|
| V_{DSS} | 55V |
| $R_{DS(on)}$ typ. | 48mΩ |
| max. | 60mΩ |
| I_D | 5.0A |



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

| Base part number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|--------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| AUIRLL024Z | SOT-223 | Tape and Reel | 2500 | AUIRLL024ZTR |

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

| Symbol | Parameter | Max. | Units |
|--------------------------------|---|---------------------------|-------|
| $I_D @ T_A = 25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑦ | 5.0 | A |
| $I_D @ T_A = 70^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑦ | 4.0 | |
| I_{DM} | Pulsed Drain Current ① | 40 | W |
| $P_D @ T_A = 25^\circ\text{C}$ | Maximum Power Dissipation (PCB Mount) ⑦ | 2.8 | |
| $P_D @ T_A = 25^\circ\text{C}$ | Maximum Power Dissipation (PCB Mount) ⑧ | 1.0 | |
| | Linear Derating Factor (PCB Mount) ⑦ | 0.02 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 16 | V |
| E_{AS} | Single Pulse Avalanche Energy (Thermally Limited) ② | 21 | mJ |
| $E_{AS (Tested)}$ | Single Pulse Avalanche Energy (Tested Value) ⑥ | 38 | |
| I_{AR} | Avalanche Current ① | See Fig. 12a, 12b, 15, 16 | A |
| E_{AR} | Repetitive Avalanche Energy ⑤ | | mJ |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 150 | °C |

Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|-----------------|---|------|------|-------|
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount, steady state) ⑦ | — | 45 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount, steady state) ⑧ | — | 120 | |

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*Qualification standards can be found at www.infineon.com

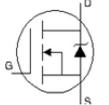
Static @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--|--------------------------------------|------|-------|------|-------|---|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 55 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.049 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 48 | 60 | mΩ | V _{GS} = 10V, I _D = 3.0A ③ |
| | | — | — | 80 | | V _{GS} = 5.0V, I _D = 3.0A ③ |
| | | — | — | 100 | | V _{GS} = 4.5V, I _D = 3.0A ③ |
| V _{GS(th)} | Gate Threshold Voltage | 1.0 | — | 3.0 | V | V _{DS} = V _{GS} , I _D = 250μA |
| g _{fs} | Forward Trans conductance | 7.5 | — | — | S | V _{DS} = 25V, I _D = 3.0A |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | V _{DS} = 55V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 55V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 200 | nA | V _{GS} = 16V |
| | Gate-to-Source Reverse Leakage | — | — | -200 | | V _{GS} = -16V |

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

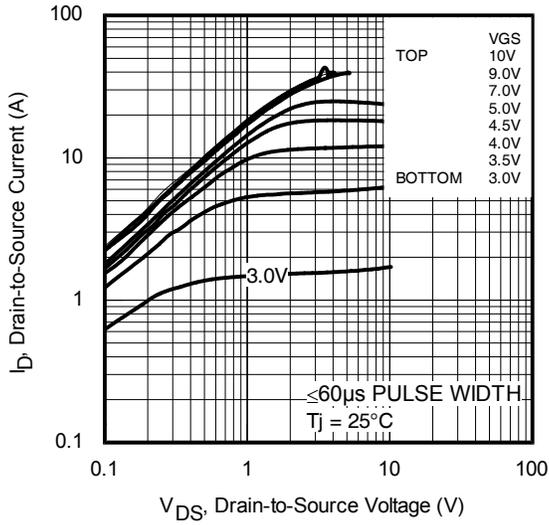
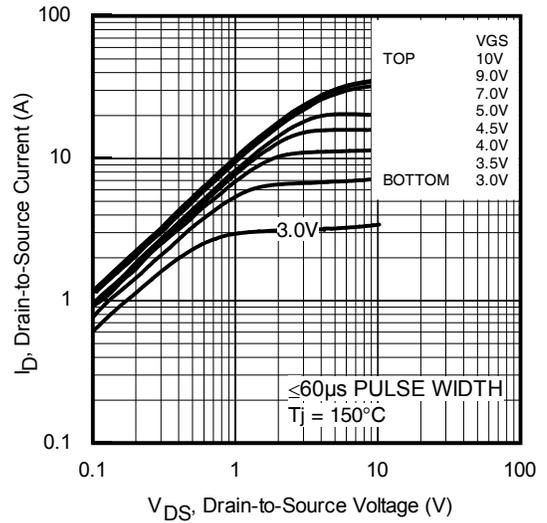
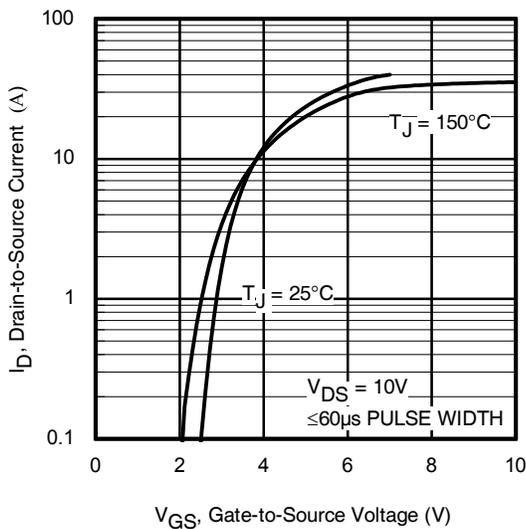
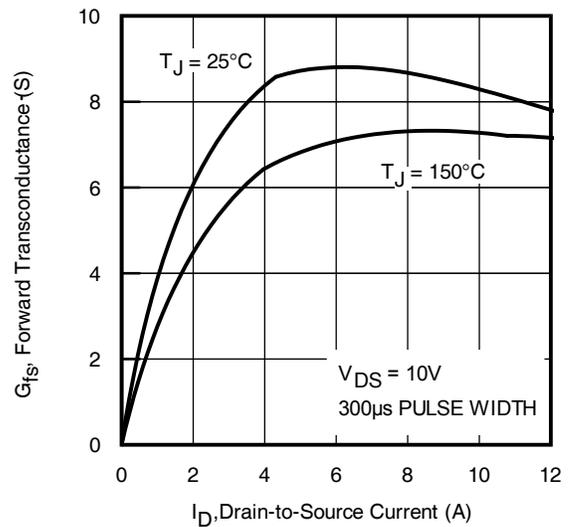
| | | | | | | |
|-----------------------|------------------------------|---|-----|----|----|--|
| Q _g | Total Gate Charge | — | 7.0 | 11 | nC | I _D = 3.0A |
| Q _{gs} | Gate-to-Source Charge | — | 1.5 | — | | V _{DS} = 44V |
| Q _{gd} | Gate-to-Drain Charge | — | 4.0 | — | | V _{GS} = 5.0V ③ |
| t _{d(on)} | Turn-On Delay Time | — | 8.6 | — | ns | V _{DD} = 28V |
| t _r | Rise Time | — | 33 | — | | I _D = 3.0A |
| t _{d(off)} | Turn-Off Delay Time | — | 20 | — | | R _G = 56Ω |
| t _f | Fall Time | — | 15 | — | | V _{GS} = 5.0V ③ |
| C _{iss} | Input Capacitance | — | 380 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 66 | — | | V _{DS} = 25V |
| C _{rss} | Reverse Transfer Capacitance | — | 36 | — | | f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 220 | — | | V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 53 | — | | V _{GS} = 0V, V _{DS} = 44V, f = 1.0MHz |
| C _{oss eff.} | Effective Output Capacitance | — | 93 | — | | V _{GS} = 0V, V _{DS} = 0V to 44V ④ |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|--|--|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 5.0 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 40 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 3.0A, V _{GS} = 0V ④ |
| t _{rr} | Reverse Recovery Time | — | 15 | 23 | ns | T _J = 25°C, I _F = 3.0A, V _{DD} = 28V |
| Q _{rr} | Reverse Recovery Charge | — | 9.1 | 14 | nC | di/dt = 100A/μs ③ |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Limited by T_{Jmax}, Starting T_J = 25°C, L = 4.8mH, R_G = 25Ω, I_{AS} = 3.A, V_{GS} = 10V. Part not recommended for use above this value.
- ③ Pulse width ≤ 1.0ms; duty cycle ≤ 2%.
- ④ C_{oss eff.} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑤ Limited by T_{Jmax}, see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value determined from sample failure population, starting T_J = 25°C, L = 4.8mH, R_G = 25Ω, I_{AS} = 3.0A, V_{GS} = 10V.
- ⑦ When mounted on 1 inch square copper board.
- ⑧ When mounted on FR-4 board using minimum recommended footprint.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Typical Forward Trans conductance vs. Drain Current

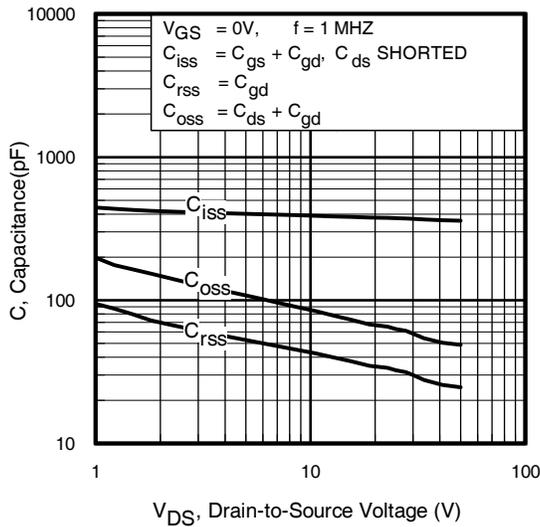


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

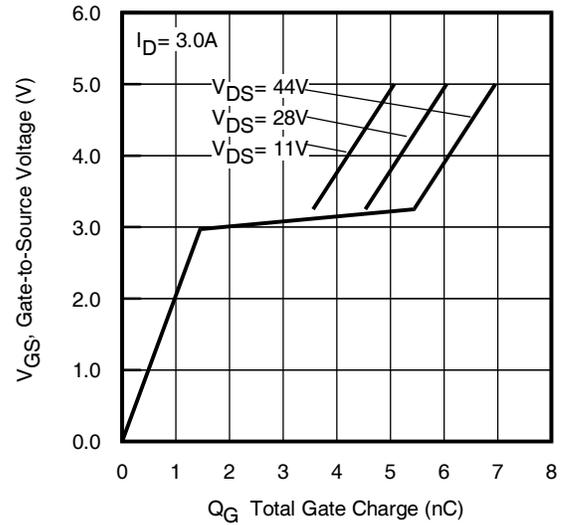


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

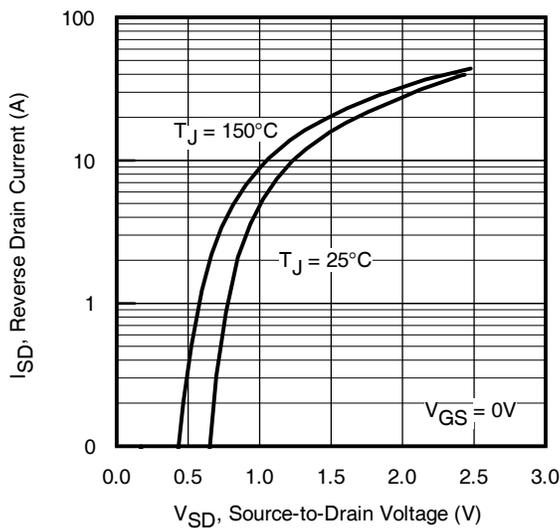


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

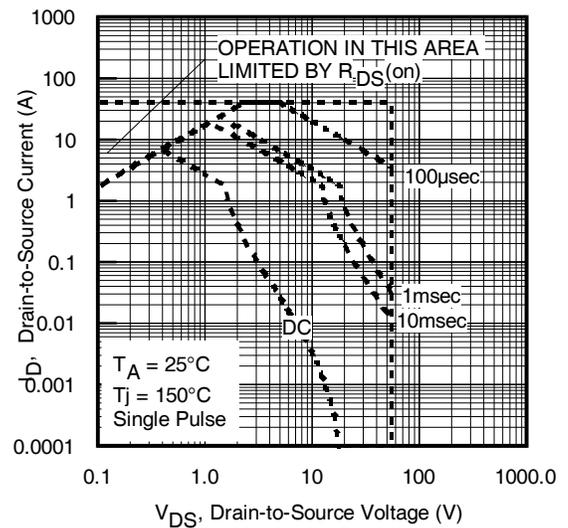
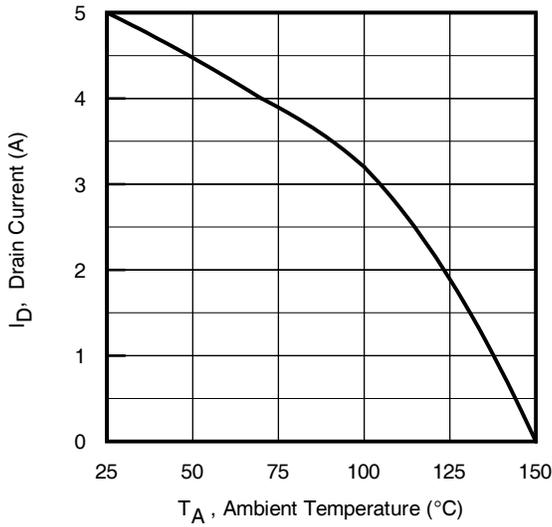
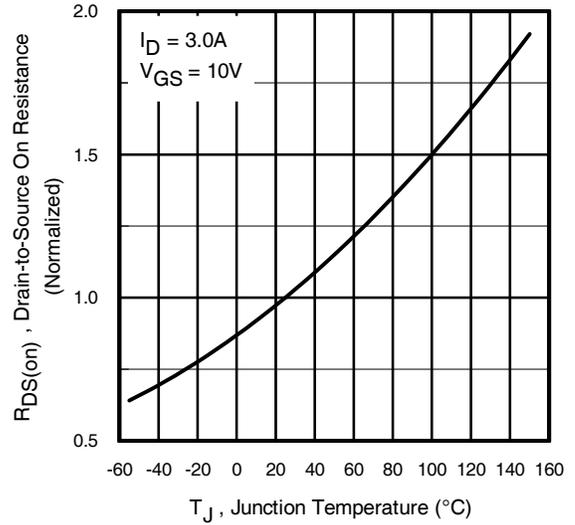
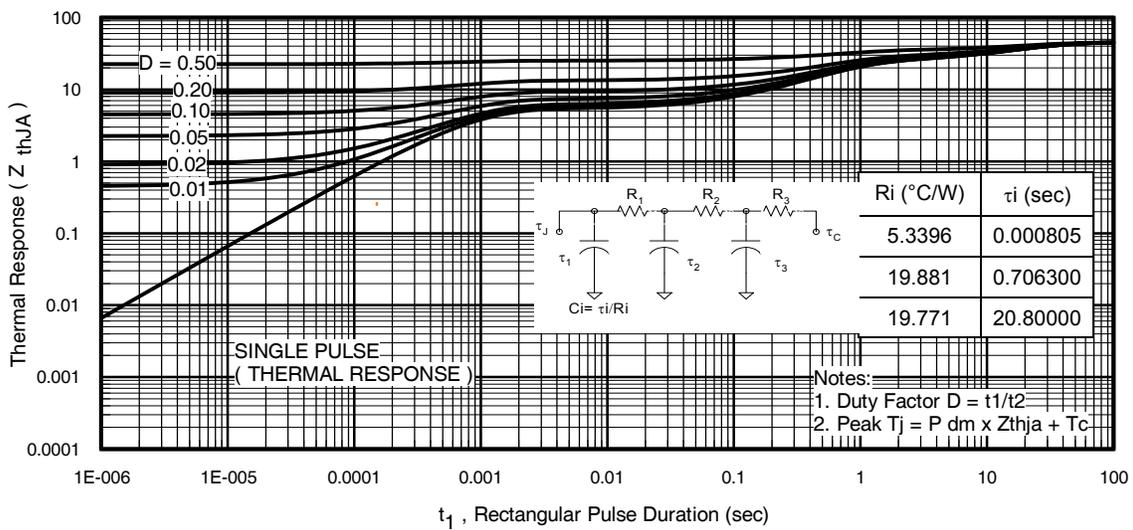
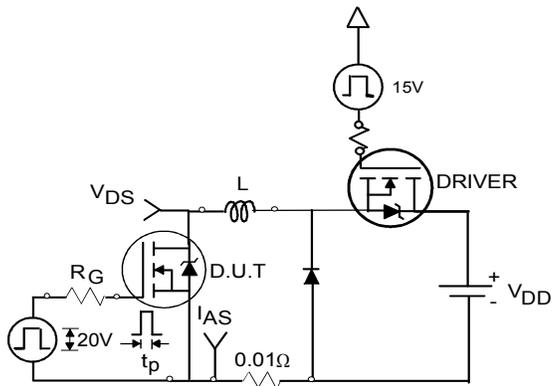
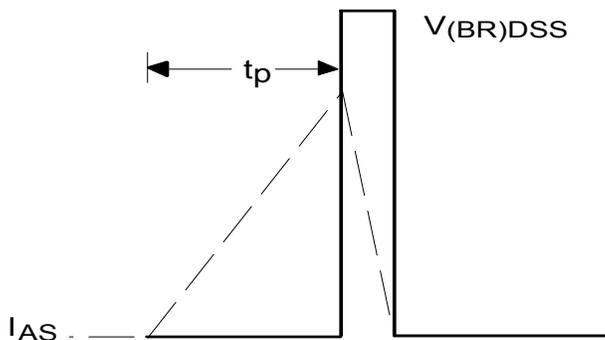
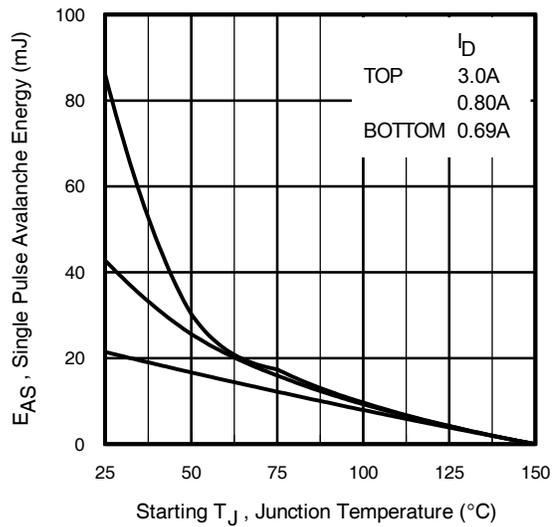
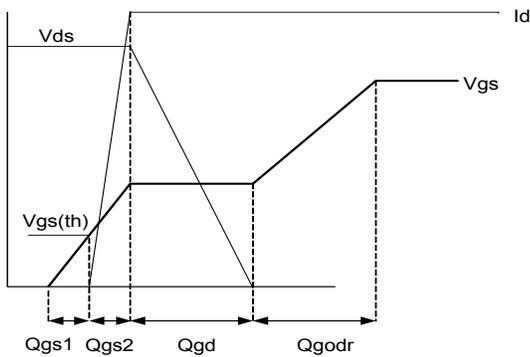
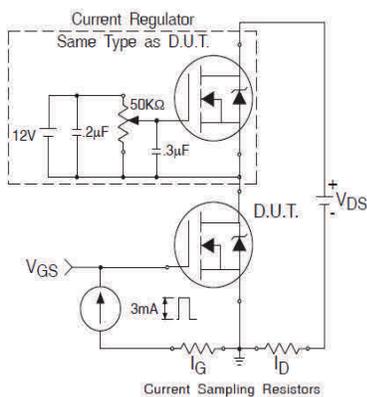
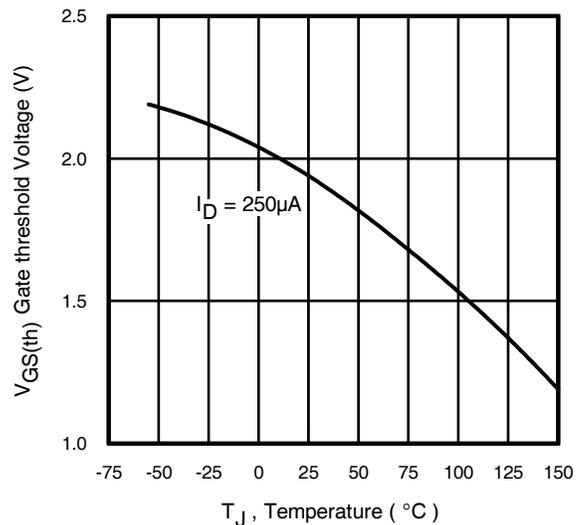
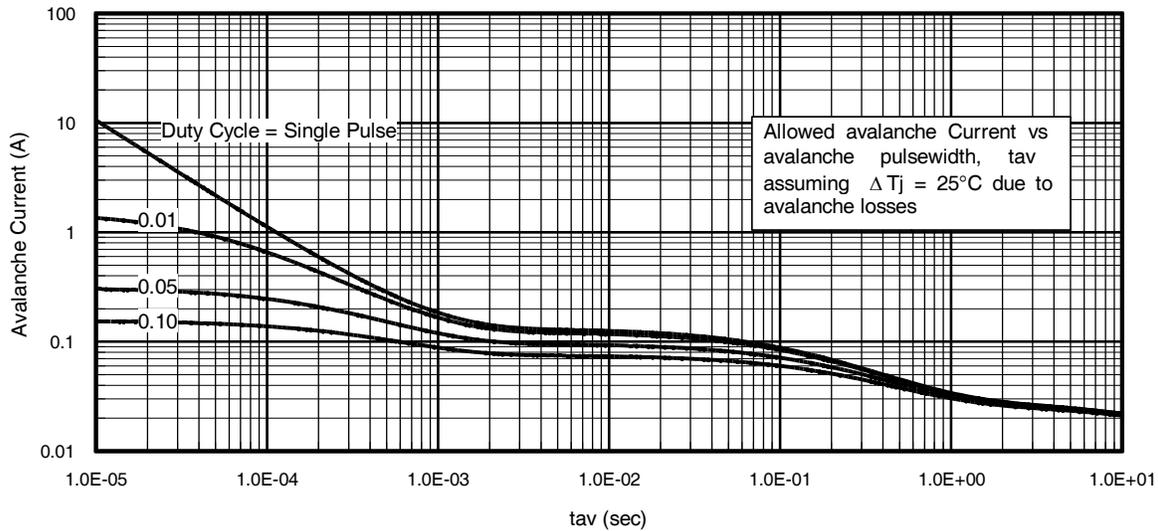
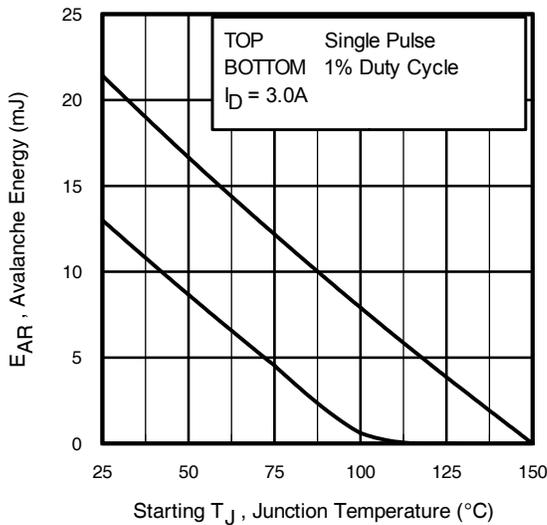


Fig 8. Maximum Safe Operating Area


Fig 9. Maximum Drain Current Vs. Ambient Temperature

Fig 10. Normalized On-Resistance vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12a. Unclamped Inductive Test Circuit

Fig 12b. Unclamped Inductive Waveforms

Fig 12c. Maximum Avalanche Energy Vs. Drain Current

Fig 13a. Basic Gate Charge Waveform

Fig 13b. Gate Charge Test Circuit

Fig 14. Threshold Voltage vs. Temperature


Fig 15. Typical Avalanche Current vs. Pulse width

Fig 16. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.infineon.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

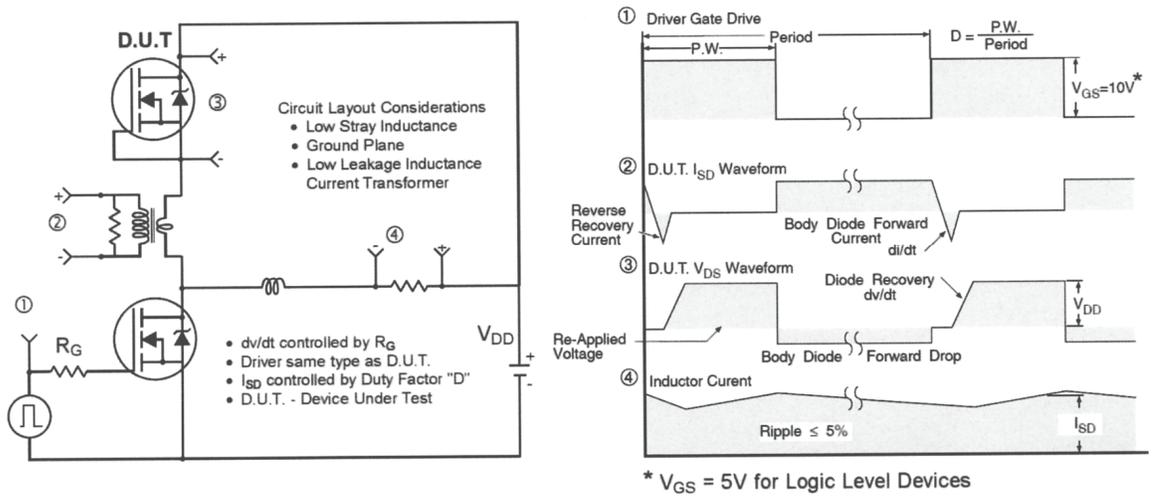


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

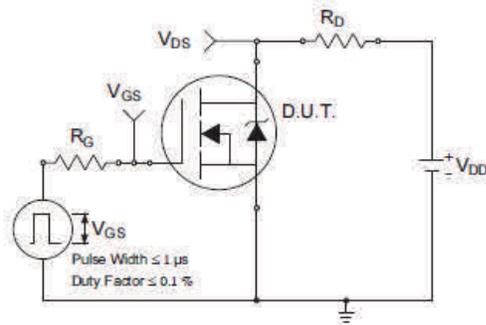


Fig 18a. Switching Time Test Circuit

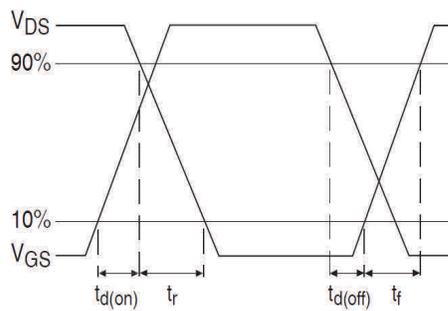
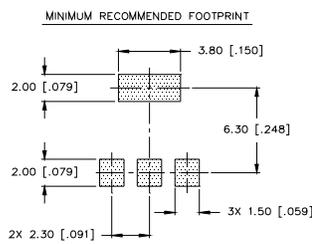
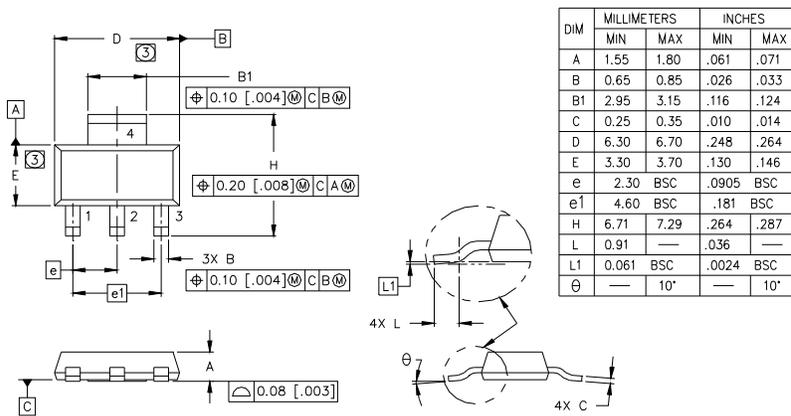


Fig 18b. Switching Time Waveforms

SOT-223 (TO-261AA) Package Outline (Dimensions are shown in millimeters (inches))

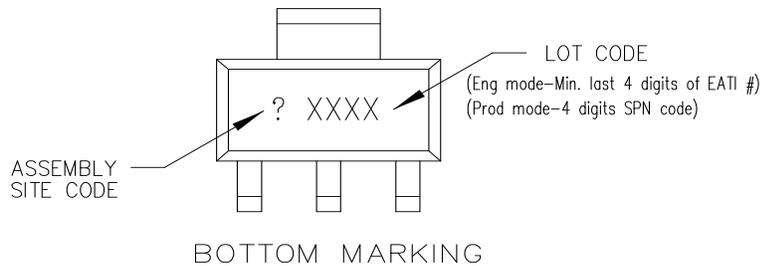
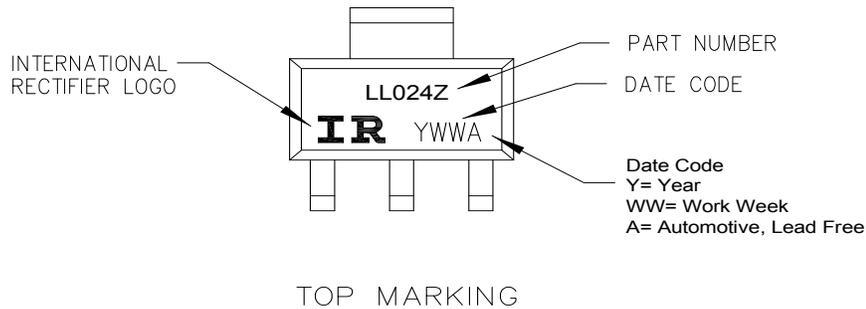


LEAD ASSIGNMENTS

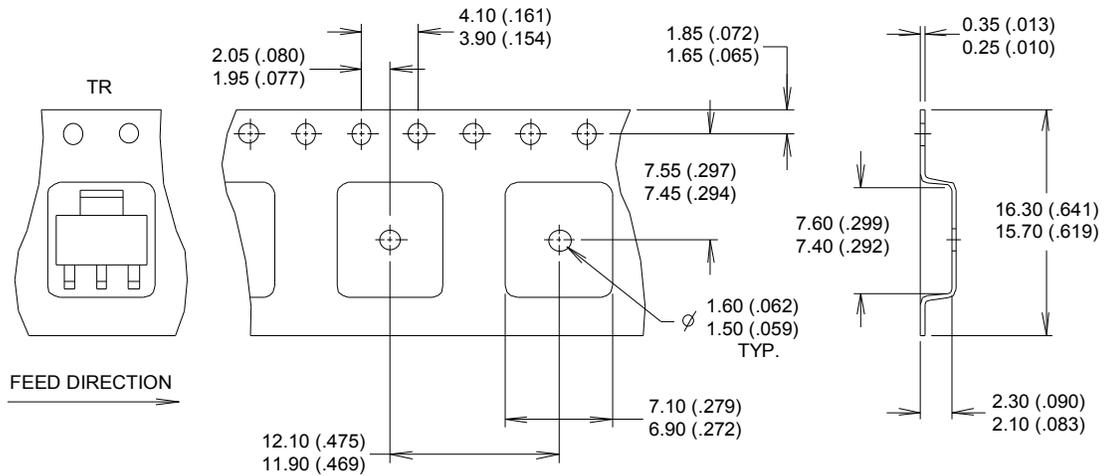
- 1 = GATE
- 2 = DRAIN
- 3 = SOURCE
- 4 = DRAIN

- NOTES:**
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSIONS DO NOT INCLUDE MOLD FLASH.
 4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
 5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

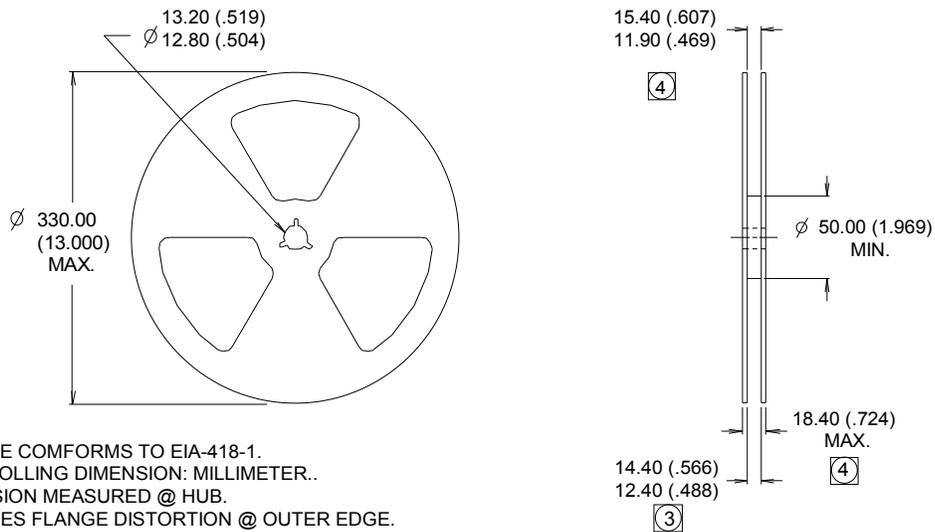
SOT-223(TO-261AA) Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

SOT-223(TO-261AA) Tape and Reel (Dimensions are shown in millimeters (inches))

NOTES :

1. CONTROLLING DIMENSION: MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.
3. EACH $\varnothing 330.00$ (13.00) REEL CONTAINS 2,500 DEVICES.


NOTES :

1. OUTLINE COMFORMS TO EIA-418-1.
2. CONTROLLING DIMENSION: MILLIMETER..
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information

| | | | |
|-----------------------------------|----------------------|---|------|
| Qualification Level | | Automotive (per AEC-Q101) | |
| | | Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| Moisture Sensitivity Level | | SOT-223 | MSL1 |
| ESD | Machine Model | Class M1B (+/- 100V) [†] AEC-Q101-002 | |
| | Human Body Model | Class H0 (+/- 250V) [†] AEC-Q101-001 | |
| | Charged Device Model | Class C5 (+/- 1125V) [†] AEC-Q101-005 | |
| RoHS Compliant | | Yes | |

† Highest passing voltage.

Revision History

| Date | Comments |
|------------|--|
| 3/26/2014 | <ul style="list-style-type: none"> Added "Logic Level Gate Drive" bullet in the features section on page 1 Updated part marking on page 9 Updated data sheet with new IR corporate template |
| 10/29/2015 | <ul style="list-style-type: none"> Updated datasheet with corporate template Corrected ordering table on page 1. |

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